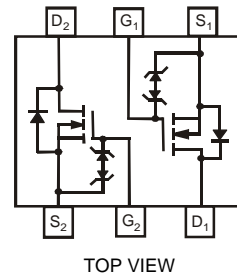
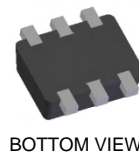


Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **ESD Protected Up To 2KV**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 6	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	1.38	A
		$T_A = 85^\circ\text{C}$		0.89	
Pulsed Drain Current (Note 4)			I_{DM}	3	A

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 3)	P_D	530	mW
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$ (Note 3)	$R_{\theta JA}$	235	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 4. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	100	nA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	0.5	-	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	0.3	0.45	Ω	V _{GS} = 4.5V, I _D = 600mA
			0.4	0.6		V _{GS} = 2.5V, I _D = 500mA
			0.5	0.75		V _{GS} = 1.8V, I _D = 350mA
			-	9		V _{GS} = 1.7V, I _D = 140mA
			-	10		V _{GS} = 1.5V, I _D = 100mA
Forward Transfer Admittance	Y _{fs}	-	1.4	-	S	V _{DS} = 10V, I _D = 400mA
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	V _{GS} = 0V, I _S = 150mA
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iss}	-	60.67	-	pF	V _{DS} = 16V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	9.68	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	5.37	-	pF	
Total Gate Charge	Q _g	-	736.6	-	pC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	-	93.6	-	pC	
Gate-Drain Charge	Q _{gd}	-	116.6	-	pC	
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 47Ω, R _G = 10Ω, I _D = 200mA
Turn-On Rise Time	t _r	-	7.4	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	26.7	-	ns	
Turn-Off Fall Time	t _f	-	12.3	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.
6. Guaranteed by design. Not subject to production testing.

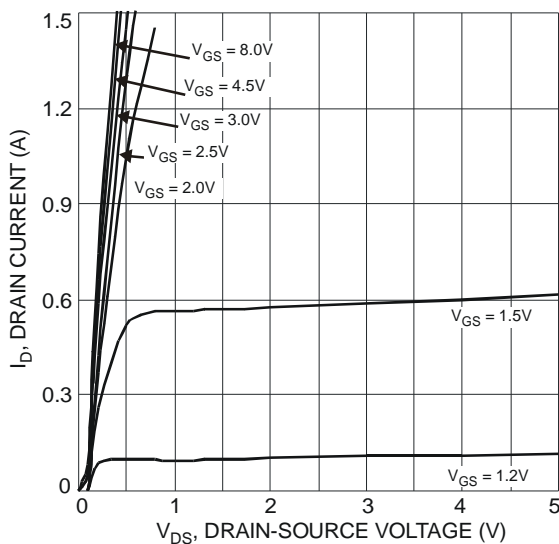


Fig. 1 Typical Output Characteristics

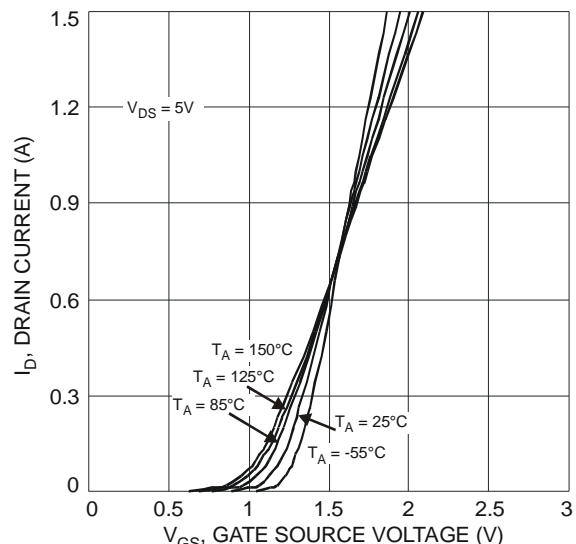


Fig. 2 Typical Transfer Characteristics

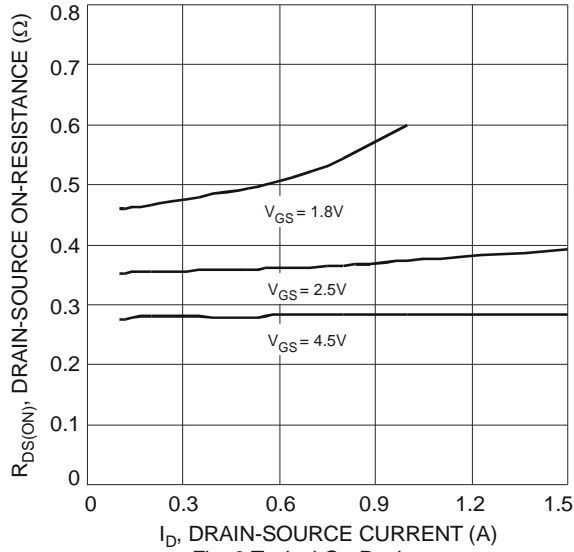


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

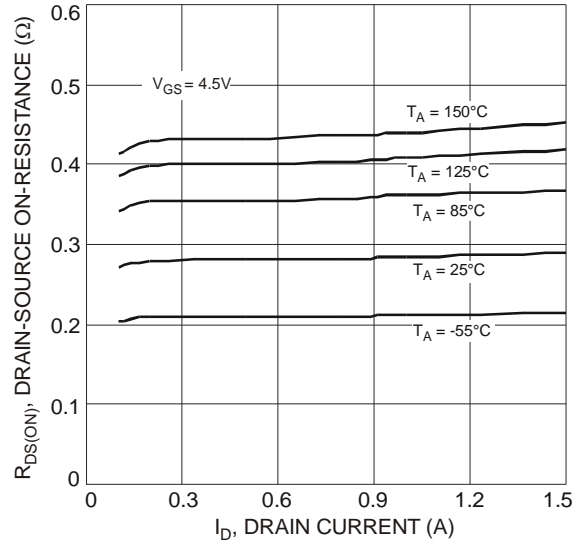


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

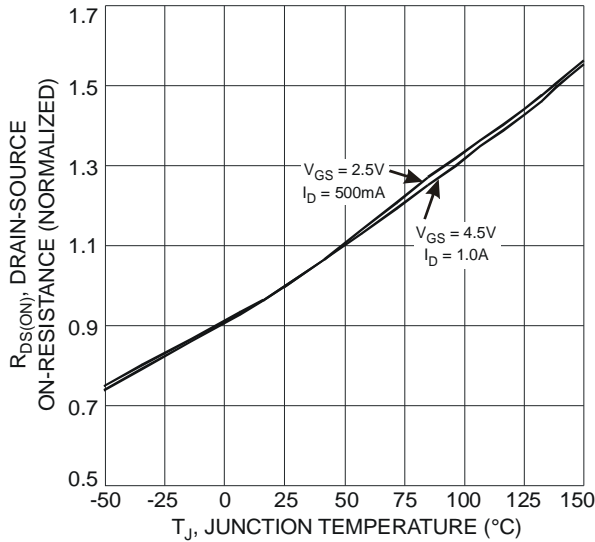


Fig. 5 On-Resistance Variation with Temperature

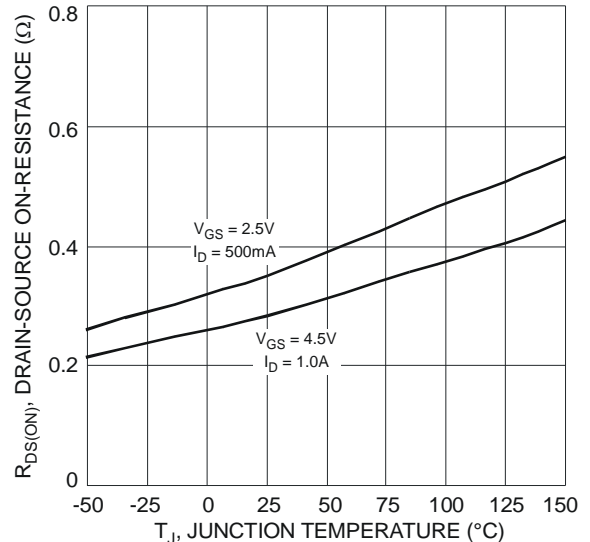


Fig. 6 On-Resistance Variation with Temperature

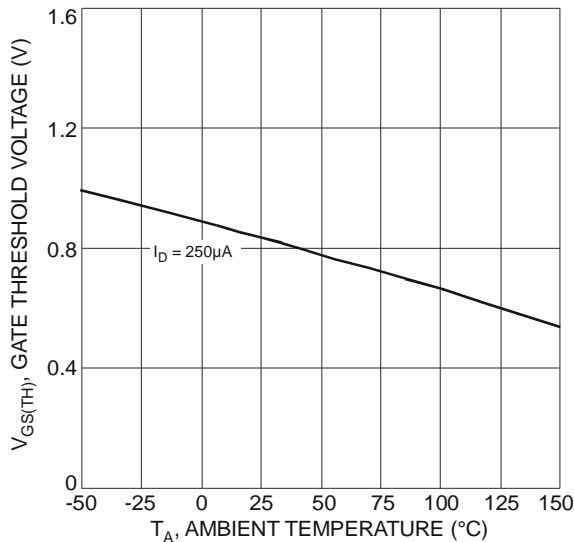


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

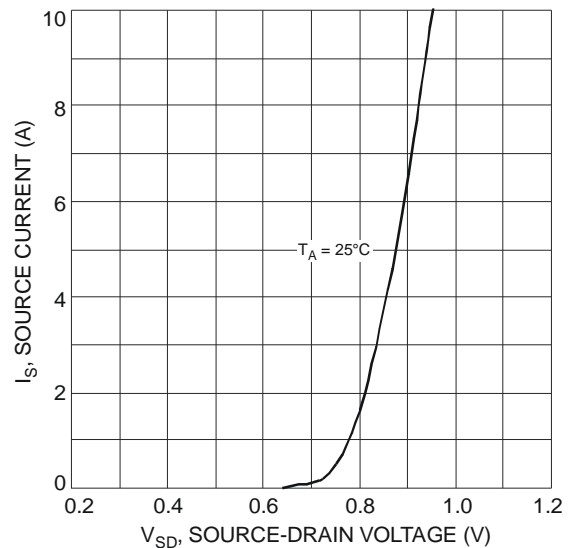
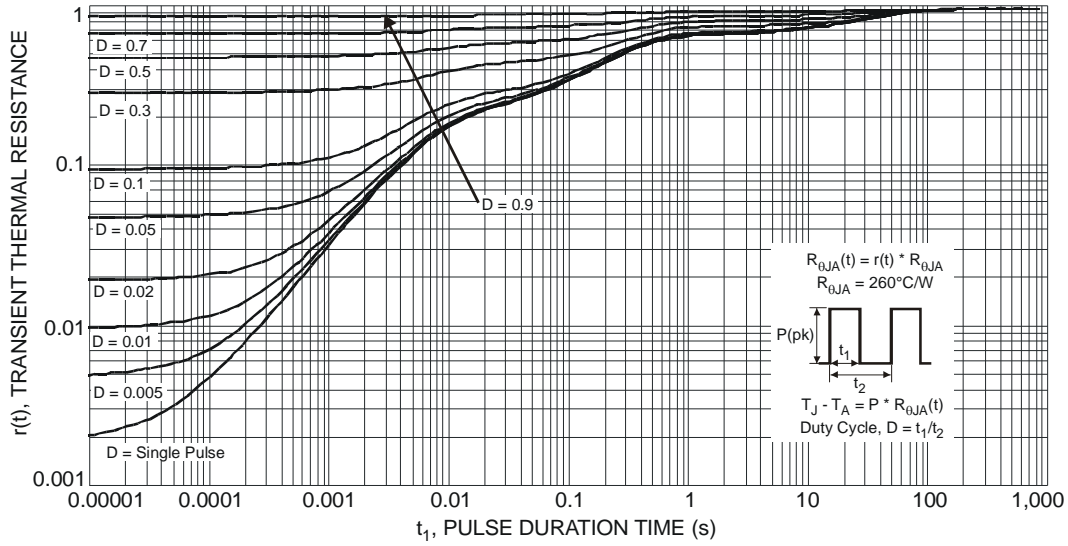
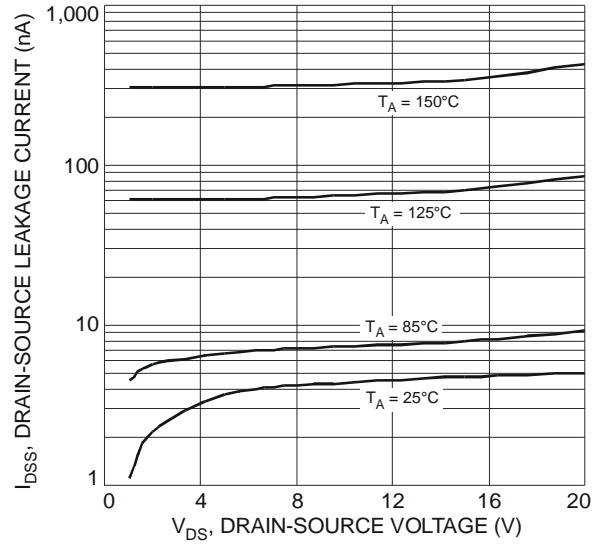
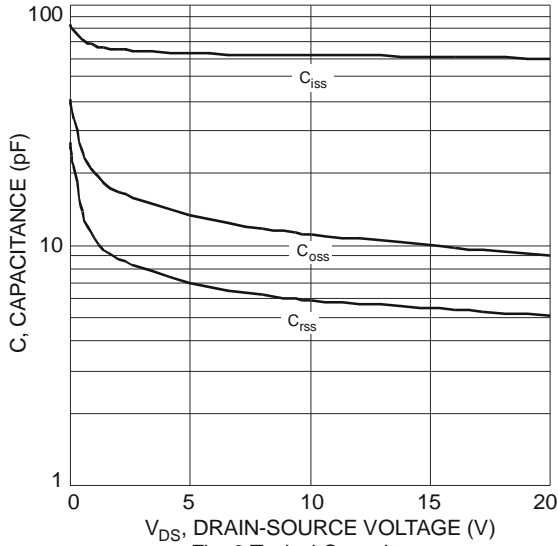


Fig. 8 Diode Forward Voltage vs. Current

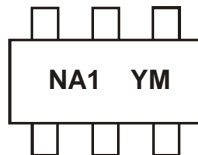


Ordering Information (Note 7)

Part Number	Case	Packaging
DMG1024UV-7	SOT-563	3000 / Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



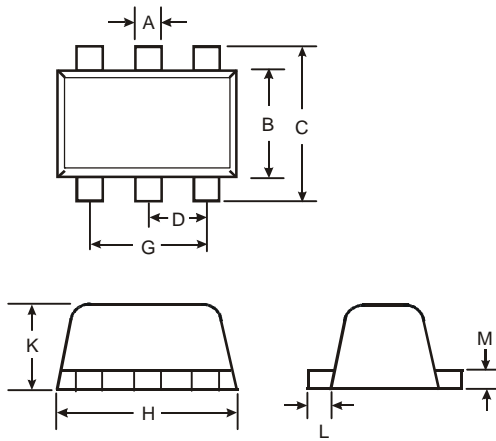
NA1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: W = 2009)
 M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

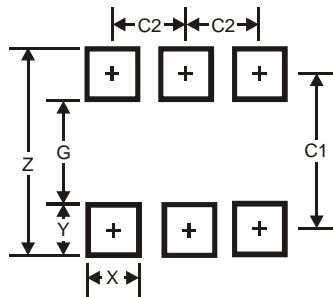
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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